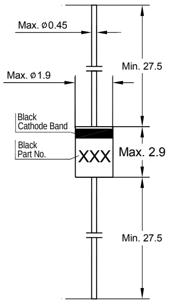
1N4531, 1N4532

Silicon Epitaxial Planar Switching Diode

Applications

- High-speed switching



Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	75	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	200	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-repetitive Peak Forward Current at t = 1 μs	I_{FSM}	4	A
at t = 1 ms		1	
at t = 1 s		0.5	
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	200	°C
Storage Temperature Range	T_{stg}	- 65 to + 200	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 10 mA	V_F	1	V
Reverse Current			
at V_R = 20 V 1N4531	I_R	25	nA
at V_R = 50 V 1N4532	I_R	100	nA
at V_R = 20 V, T_j = 150 °C 1N4531	I_R	50	μA
at V_R = 50 V, T_j = 150 °C 1N4532	I_R	100	μA
Diode Capacitance at V_R = 0 , f = 1 MHz 1N4531	C_d	4	pF
1N4532	C_d	2	pF
Reverse Recovery Time			
at I_F = 10 mA, I_R = 60 mA, R_L = 100 Ω 1N4531	t_{rr}	4	ns
1N4532	t_{rr}	2	ns
at I_F = 10 mA, I_R = 10 mA, R_L = 100 Ω 1N4532	t_{rr}	4	ns

Dated : 15/06/2009